

The documentation and process conversion measures necessary to comply with this document shall be completed by 7 August, 2003.

INCH-POUND
MIL-PRF-19500/710
7 May 2003

PERFORMANCE SPECIFICATION

SEMICONDUCTOR DEVICE, TRANSISTOR, NPN, SILICON, POWER
TYPES 2N6674T1, 2N6674T3, 2N6675T1, 2N6675T3,
JAN, JANTX, AND JANTXV

This specification is approved for use by all Departments and Agencies of the Department of Defense.

1. SCOPE

1.1 Scope. This specification covers the performance requirements for NPN, silicon, power transistors for use in high-speed power-switching applications. Three levels of product assurance are provided for each device type as specified in MIL-PRF-19500.

1.2 Physical dimensions. See figure 1 (TO-254AA) and figure 2 (TO-257AA).

1.3 Maximum ratings.

Type	P _T (1)		V _{CB0} and V _{CEX}	V _{CEO}	V _{EBO}	I _B	I _C	T _J and T _{STG}
	T _A = +25°C	T _C = +25°C						
	<u>W</u>	<u>W</u>	<u>V dc</u>	<u>V dc</u>	<u>V dc</u>	<u>A dc</u>	<u>A dc</u>	<u>°C</u>
2N6674T1	6	(2) 175	450	300	7	5	15	
2N6674T3	4	(2) 175	450	300	7	5	15	-65 to +200
2N6675T1	6	(2) 175	650	400	7	5	15	
2N6675T3	4	(2) 175	650	400	7	5	15	

(1) For derating, see figures 3 and 4. For thermal impedance curves, see figures 5 and 6.

(2) For TO-257 devices, ratings at 125W and 1.3°C/W only.

Beneficial comments (recommendations, additions, deletions) and any pertinent data which may be of use in improving this document should be addressed to: Defense Supply Center, Columbus, ATTN: DSCC-VAC, P.O. Box 3990, Columbus, OH 43216-5000, by using the Standardization Document Improvement Proposal (DD Form 1426) appearing at the end of this document or by letter.

1.4 Primary electrical characteristics at $T_C = +25^\circ\text{C}$.

Limit	$R_{\theta JC}$ T1 only (1)	$R_{\theta JC}$ T3 only (1)	$V_{BE(sat)}$ $I_C = 10\text{ A dc}$ $I_B = 2\text{ A dc}$	$V_{CE(sat)}$ $I_C = 10\text{ A dc}$ $I_B = 2\text{ A dc}$	C_{obo} $V_{CB} = 10\text{ V dc}$ $I_E = 0\text{ A dc}$ $100\text{ kHz} < f < 1\text{ MHz}$	$ h_{fe} $ $V_{CE} = 10\text{ V dc}$ $I_C = 1\text{ A dc}$ $f = 5\text{ MHz}$
	$^\circ\text{C/W}$	$^\circ\text{C/W}$	V dc	V dc	pF	
Min					150	3
Max	1.0	1.3	1.5	1.0	500	10

Limit	h_{FE1} $V_{CE} = 3\text{ V dc}$ $I_C = 1\text{ A dc}$	h_{FE2} $V_{CE} = 2\text{ V dc}$ $I_C = 10\text{ A dc}$ (2)	Switching parameters				
			t_d	t_r	t_s	t_f	t_c
Min	15	8	μs	μs	μs	μs	μs
Max	40	20	0.1	0.6	2.5	0.5	0.5

- (1) For thermal impedance curves, see figures 5 and 6.
- (2) Pulsed (see 4.5.1).

2. APPLICABLE DOCUMENTS

2.1 General. The documents listed in this section are specified in sections 3 and 4 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements documents cited in sections 3 and 4 of this specification, whether or not they are listed.

2.2 Government documents.

2.2.1 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DoDISS) and supplement thereto, cited in the solicitation (see 6.2).

SPECIFICATION

DEPARTMENT OF DEFENSE

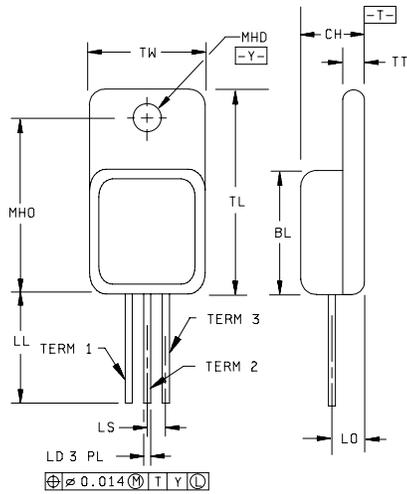
MIL-PRF-19500 - Semiconductor Devices, General Specification for.

STANDARD

DEPARTMENT OF DEFENSE

MIL-STD-750 - Test Methods for Semiconductor Devices.

(Unless otherwise indicated, copies of the above specifications, standards, and handbooks are available from the Document Automation and Production Services (DAPS), Building 4D (DPM-DODSSP), 700 Robbins Avenue, Philadelphia, PA 19111-5094.)

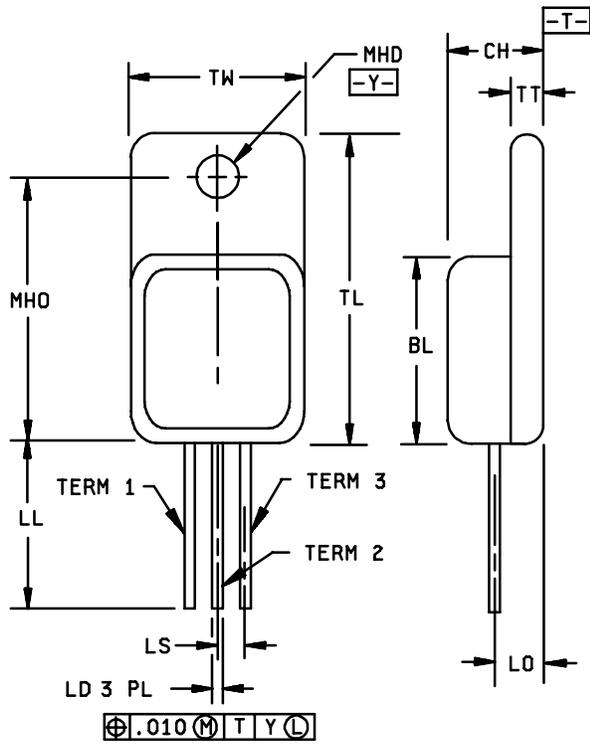


NOTES:

1. Dimensions are in inches.
2. Millimeters equivalents are given for general information only.
3. All terminals are isolated from case.
4. Methods used for electrical isolation of the terminals feedthroughs shall employ materials that contain a minimum of 90 percent AL₂O₃ (ceramic).

Ltr	Dimensions			
	Inches		Millimeters	
	Min	Max	Min	Max
BL	.535	.545	13.59	13.89
CH	.249	.260	6.32	6.60
LD	.035	.045	0.89	1.43
LL	.530	.550	13.46	13.97
LO	.150 BSC		3.81 BSC	
LS	.150 BSC		3.81 BSC	
MHD	.139	.149	3.53	3.78
MHO	.665	.685	16.89	17.40
TL	.790	.800	20.07	20.32
TT	.040	.050	1.02	1.27
TW	.535	.545	13.59	13.89
Term 1	Base			
Term 2	Collector			
Term 3	Emitter			

FIGURE 1. Dimensions and configuration 2N6674T1 and 2N6675T1 (TO-25AA).



Ltr	Dimensions			
	Inches		Millimeters	
	Min	Max	Min	Max
BL	.410	.430	10.41	10.92
CH	.190	.200	4.83	5.08
LD	.025	.035	0.64	0.89
LL	.500	.750	12.70	19.05
LS	.100 BSC		2.54 BSC	
MHD	.140	.150	3.56	3.81
MHO	.527	.537	13.39	13.63
TL	.645	.665	16.38	16.89
TT	.035	.045	0.89	1.14
TW	.410	.420	10.41	10.67
Term 1	Base			
Term 2	Collector			
Term 3	Emitter			

NOTES:

1. Dimensions are in inches.
2. Metric equivalents are given for general information only.
3. Methods used for electrical isolation of the terminals feedthroughs shall employ materials that contain a minimum of 90 percent AL₂O₃ (ceramic).
4. In accordance with ASME Y14.5M, diameters are equivalent to ϕ x symbology.

FIGURE 2. Dimensions and configuration for 2N6674T3 and 2N6675T3 (TO-257AA).

2.3 Order of precedence. In the event of a conflict between the text of this document and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 General. The individual item requirements shall be as specified in MIL-PRF-19500 and as modified herein.

3.2 Qualification. Devices furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturer's list (QML) before contract award (see 4.2 and 6.3).

3.3 Abbreviations, symbols, and definitions. Abbreviations, symbols, and definitions used herein shall be as specified in MIL-PRF-19500.

3.4 Interface and physical dimensions. Interface and physical dimensions shall be as specified in MIL-PRF-19500, and on figure 1 and figure 2.

3.4.1 Lead finish. Lead finish shall be solderable in accordance with MIL-PRF-19500, MIL-STD-750, and herein. Where a choice of lead finish is desired, it shall be specified in the acquisition document (see 6.2).

3.5 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in 1.3, 1.4, and table I.

3.6 Electrical test requirements. The electrical test requirements shall be table I, group A as specified herein.

3.7 Marking. Marking shall be in accordance with MIL-PRF-19500.

3.8 Workmanship. Semiconductor devices shall be processed in such a manner as to be uniform in quality and shall be free from other defects that will affect life, serviceability, or appearance.

4. VERIFICATION

4.1 Classification of inspections. The inspection requirements specified herein are classified as follows:

- a. Qualification inspection (see 4.2).
- b. Screening (see 4.3).
- c. Conformance inspection (see 4.4, and tables I, II, and III).

4.2 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-19500 and as specified herein.

4.2.1 Group E qualification. Group E qualification shall be performed herein for qualification or requalification only. In case qualification was awarded to a prior revision of the associated specification that did not request the performance of table III tests, the tests specified in a table III herein shall be performed by the first inspection lot to this revision to maintain qualification.

4.3 Screening (JANTX, and JANTXV levels only). Screening shall be in accordance with table IV of MIL-PRF-19500 and as specified herein. The following measurements shall be made in accordance with table I herein. Devices that exceed the limits of table I herein shall not be acceptable.

Screen (see table II of MIL-PRF-19500)	Measurement
	JANTX and JANTXV levels
3c	Thermal impedance, method 3131 MIL-STD-750
9	I_{CEX1}
11	I_{CEX1} and h_{FE2} ; ΔI_{CEX1} = 100 percent of initial value or 50 μ A dc, whichever is greater.
12	See 4.2.1
13a	Subgroup 2 of table I herein; ΔI_{CEX1} = 100 percent of initial value or 50 μ A dc, whichever is greater; h_{FE2} = ± 20 percent of initial value.

4.3.1 Power burn-in conditions. Power burn-in conditions are as follows: $T_J = +175^\circ\text{C}$ minimum; $V_{CB} = 100$ V dc; $T_A \leq +35^\circ\text{C}$.

4.4 Conformance inspection. Conformance inspection shall be in accordance with MIL-PRF-19500 and as specified herein.

4.4.1 Group A inspection. Group A inspection shall be conducted in accordance with MIL-PRF-19500, and table I herein. Electrical measurements (end-points) shall be in accordance with table I, subgroup 2 herein.

4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the conditions specified for subgroup testing in table VIb (JAN, JANTX, and JANTXV) and in 4.4.2.1 herein. Electrical measurements (end-points) shall be in accordance with table I, subgroup 2 herein. Delta requirements shall be in accordance with table II herein.

4.4.2.1 Group B inspection, table VIb of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Inspection</u>
B3	1027	For eutectic die attach: $V_{CB} \geq 100$ V dc; adjust P_T to achieve $T_J = +175^\circ\text{C}$ minimum; $T_A \leq +35^\circ\text{C}$.
B3	1037	For solder die attach: 2,000 cycles, $V_{CB} \geq 100$ V dc.
B5	3131	See thermal impedance curves figures 5 and 6.

4.4.3 Group C inspection. Group C inspection shall be conducted in accordance with the conditions specified for subgroup testing in table VII of MIL-PRF-19500 and herein. Electrical measurements (end-points) shall be in accordance with group A, subgroup 2 herein. Delta requirements shall be in accordance with table II herein.

4.4.3.1 Group C inspection, table VII, of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Inspection</u>
C2	2036	Test condition A; weight = 10 pounds; time = 15 s.
C2	2036	Test condition D1; torque = 6 inch-ounce; time = 15 s.
C6	1027	For eutectic die attach: $V_{CB} \geq 100$ V dc; adjust P_T to achieve $T_J = +175^\circ$ C minimum, $T_A \leq +35^\circ$ C.
C6	1037	For solder die attach: 6,000 cycles, $V_{CB} \geq 100$ V dc.

4.4.4 Group E inspection. Group E inspection shall be conducted in accordance with the conditions specified for subgroup testing in appendix E, table IX of MIL-PRF-19500 and as specified herein. Electrical measurements (end-points) shall be in accordance with table I, subgroup 2 herein.

4.5 Method of inspection. Methods of inspection shall be as specified in the appropriate tables and as follows.

4.5.1 Pulse measurements. Conditions for pulse measurement shall be as specified in section 4 of MIL-STD-750.

TABLE I. Group A inspection.

Inspection <u>1</u> /	MIL-STD-750		Symbol	Limit		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 1</u>						
Visual and mechanical examination	2071					
<u>Subgroup 2</u>						
Collector to base breakdown voltage 2N6674T1, 2N6674T3 2N6675T1, 2N6675T3	3011	Bias condition D; $I_C = 200$ mA dc; pulsed (see 4.5.1)	$V_{(BR)CEO}$	300 400		V dc
Collector to emitter cutoff current 2N6674T1, 2N6674T3 2N6675T1, 2N6675T3	3041	Bias condition D; $V_{BE} = -1.5$ V dc $V_{CE} = 450$ V dc $V_{CE} = 650$ V dc	I_{CEX1}		0.1	mA dc
Collector to base cutoff current 2N6674T1, 2N6674T3 2N6675T1, 2N6675T3	3036	Bias condition D; $V_{CB} = 450$ V dc $V_{CB} = 650$ V dc	I_{CBO}		1.0	mA dc
Emitter-base cutoff current	3061	Bias condition D, $V_{EB} = 7$ V dc	I_{EBO}		2.0	mA dc
Base emitter voltage	3066	Test condition A; $I_C = 10$ A dc; pulsed (see 4.5.1); $I_B = 2$ A dc	$V_{BE(sat)}$		1.5	V dc
Collector to emitter saturated Voltage	3071	$I_C = 10$ A dc; pulsed (see 4.5.1) $I_B = 2$ A dc	$V_{CE(sat)1}$		1.0	V dc
Collector to emitter saturated Voltage	3071	$I_C = 15$ A dc; pulsed (see 4.5.1) $I_B = 5$ A dc	$V_{CE(sat)2}$		5.0	V dc
Forward-current transfer ratio	3076	$V_{CE} = 3$ V dc; $I_C = 1$ A dc; pulsed (see 4.5.1)	h_{FE1}	15	40	
Forward-current transfer ratio	3076	$V_{CE} = 2$ V dc; $I_C = 10$ A dc; pulsed (see 4.5.1)	h_{FE2}	8	20	

See footnote at end of table.

TABLE I. Group A inspection - Continued.

Inspection 1/	MIL-STD-750		Symbol	Limit		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 3</u>						
High-temperature operation:		$T_A = +125^\circ\text{C}$				
Collector to emitter cutoff current	3041	Bias condition A; $V_{BE} = -1.5$ V dc	I_{CEX2}			
2N6674T1, 2N6674T3		$V_{CE} = 450$ V dc			1.0	mA dc
2N6675T1, 2N6675T3		$V_{CE} = 650$ V dc			1.0	mA dc
Collector to emitter cutoff current	3041	$T_A = +125^\circ\text{C}$, Bias condition A	I_{CEO}			
2N6674T1, 2N6674T3		$V_{CE} = 300$ V dc			90	μA
2N6675T1, 2N6675T3		$V_{CE} = 400$ V dc			90	μA
Collector to emitter saturated voltage	3071	$I_C = 10$ A dc; $I_B = 2$ A dc; pulsed (see 4.5.1)	$V_{CE(sat)2}$		2.0	V dc
Switching parameters:		$T_A = +125^\circ\text{C}$				
Pulse delay time		See figure 7	t_d		0.1	μs
Pulse rise time		See figure 7	t_r		1.0	μs
Pulse storage time		See figure 7	t_s		4.0	μs
Pulse fall time		See figure 7	t_f		1.0	μs
Cross over time		See figure 7	t_c		0.8	μs
Low-temperature operation:		$T_A = -55^\circ\text{C}$				
Forward-current transfer ratio	3076	$V_{CE} = 2$ V dc; $I_C = 10$ A dc; pulsed (see 4.5.1)	h_{FE3}	4		
<u>Subgroup 4</u>						
Magnitude of common emitter small-signal short-circuit forward-current transfer ratio	3306	$V_{CE} = 10$ V dc; $I_C = 1$ A dc; $f = 5$ MHz	$ h_{fe} $	3	10	
Open capacitance (open circuit)	3236	$V_{CB} = 10$ V dc; $I_E = 0$; 100 kHz $\leq f \leq 1.0$ MHz	C_{obo}	150	500	pF
Switching parameters:		$T_A = +125^\circ\text{C}$				
Pulse delay time		See figure 7	t_d		0.1	μs

See footnote at end of table.

TABLE I. Group A inspection - Continued.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limit		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 4 - Continued</u>						
Pulse rise time		See figure 7	t_r		0.6	μs
Pulse storage time		See figure 7	t_s		2.5	μs
Pulse fall time		See figure 7	t_f		0.5	μs
Cross over time		See figure 7	t_c		0.5	μs
<u>Subgroup 5</u>						
Safe operating area	3051	$T_C = +25^\circ\text{C}$ $t = 1 \text{ s}; 1 \text{ cycle};$ (See figure 8)				
<u>Test 1</u> 2N6674T1, 2N6674T3 2N6675T1, 2N6675T3		$V_{CE} = 11.7 \text{ V dc}; I_C = 15 \text{ A dc}$				
<u>Test 2</u> 2N6674T1, 2N6674T3 2N6675T1, 2N6675T3		$V_{CE} = 30 \text{ V dc}; I_C = 5.9 \text{ A dc}$				
<u>Test 3</u> 2N6674T1, 2N6674T3 2N6675T1, 2N6675T3		$V_{CE} = 100 \text{ V dc}; I_C = 0.25 \text{ A dc}$				
<u>Test 4</u> 2N6674T1, 2N6674T3 2N6675T1, 2N6675T3		$V_{CE} = 300 \text{ V dc}; I_C = 20 \text{ mA dc}$ $V_{CE} = 400 \text{ V dc}; I_C = 10 \text{ mA dc}$				
Safe operating area	3053	$T_A = +25^\circ\text{C}, V_{CC} = 15 \text{ V dc}$ (see figure 8); load condition B, $V_{BB2} = 5.0 \text{ V},$ $R_{BB1} = 5 \Omega; R_{BB2} = 1.5 \Omega; L = 50 \mu\text{H};$ R of inductor = $0.05 \Omega,$ $R_{load} = R \text{ of inductor}$				
2N6674T1, 2N6674T1		Clamp voltage = $350 \text{ V dc}; I_C = 15 \text{ A dc}$				
2N6675T1, 2N6675T1		Clamp voltage = $450 \text{ V dc}; I_C = 15 \text{ A dc}$				
Electrical measurements		Table I, subgroup 2 herein.				
<u>Subgroups 6 and 7</u>						
Not applicable						

1/ For sampling plan see MIL-PRF-19500.

TABLE II. Groups A, B, and C delta electrical measurements. 1/ 2/

Steps	Inspection 3/	MIL-STD-750		Symbol	Limits		Unit
		Method	Conditions		Min	Max	
1.	Collector to emitter cutoff current 2N6674T1, T3 2N6675T1, T3	3041	Bias condition A; $V_{BE} = -1.5$ V dc $V_{CE} = 450$ V dc $V_{CE} = 650$ V dc	ΔI_{CEX1} 4/	100 percent of initial value or 50 μ A whichever is greater.		
2.	Forward - current transfer ratio	3076	$V_{CE} = 3$ V dc; $I_C = 15$ A dc; pulsed (see 4.5.1)	Δh_{FE2}	± 25 percent change from initial reading.		
3.	Collector to emitter voltage (saturated)	3071	$I_C = 15$ A dc; $I_B = 3$ A dc, pulsed (see 4.5.1)	$\Delta V_{CE(sat)1}$	± 100 mV change from previously measured value.		

1/ The delta electrical measurements for table VIb (JAN, JANTX and JANTXV) of MIL-PRF-19500 are as follows:

- a. Subgroup 3, see table II herein, steps 1 and 2.
- b. Subgroup 6, see table II herein, step 2.

2/ The delta electrical measurements for table VII of MIL-PRF-19500 are as follows:

- a. Subgroup 2, see table II herein, step 1.
- b. Subgroup 3, see table II herein, step 1.
- c. Subgroup 6, see table II herein, steps 1, 2 and 3.

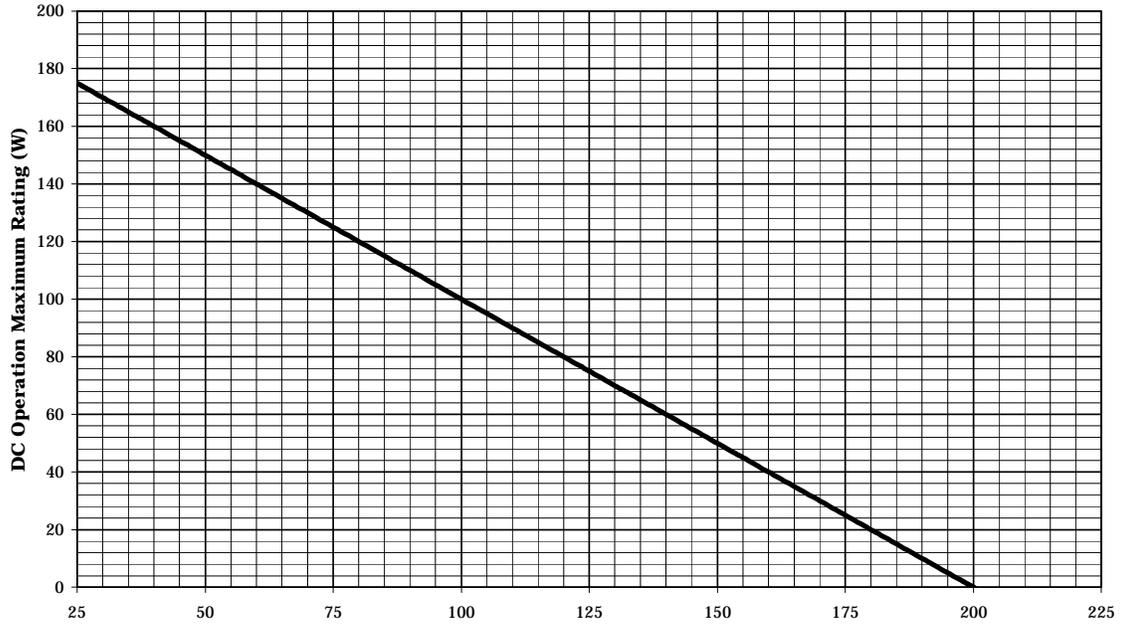
3/ See MIL-PRF-19500 for sampling plan.

4/ Devices which exceed the group A limits for this test shall not be acceptable.

TABLE III. Group E inspection (all quality levels) - for qualification and requalification only.

Inspection	MIL-STD-750		Qualification
	Method	Conditions	
<u>Subgroup 1</u>			
Temperature cycling (air to air)	1051	Test condition C, 500 cycles.	45 devices c = 0
Hermetic seal	1071		
Fine leak			
Gross leak			
Electrical measurements		See table I, subgroup 2 and 4.5.3 herein.	
<u>Subgroup 2</u>			
Intermittent life	1037	Intermittent operation life: $V_{CB} = 10$ V dc, 6,000 cycles.	45 devices c = 0
Electrical measurements		See table I, subgroup 2 and 4.5.3 herein.	
<u>Subgroups 3</u>			
DPA	2102		3 devices c = 0
<u>Subgroup 4</u>			
Thermal impedance curves		See figures 5 and 6.	
<u>Subgroup 5</u>			
Barometric pressure (reduced)	1001	$V_{DS} + \text{rated } V \text{ ISO } V \text{ dc}; I(\text{ISO}) < 0.25 \text{ mA}$	12 devices, c = 0
<u>Subgroups 6, and 7</u>			
Not applicable			
<u>Subgroup 8</u>			
Reverse stability	1033	Condition A for devices ≥ 400 v, condition B for devices < 400 v.	45 devices c = 0

Temperature-Power Derating Curves
TO254AA



DC operation Case Temperature
Thermal Resistance Junction to Case ($R_{\theta JC}$) = 1.0°C/W
Note: Maximum Finish-Alloy Temperature = 175°C for lead tin solder alloys.

FIGURE 3. Derating for TO-254AA types.

MAXIMUM-POWER DERATING CURVE
TO257AA



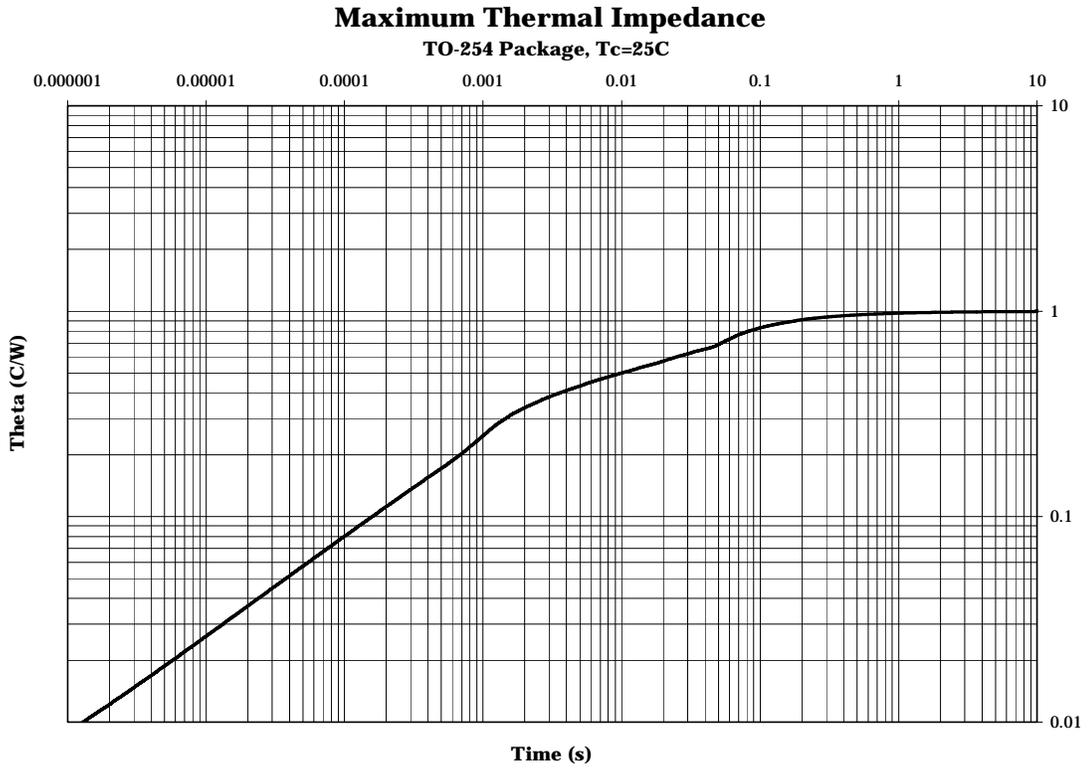
DC operation

Case Temperature

Thermal Resistance Junction to Case ($R_{\theta JC}$) = 1.3°C/W

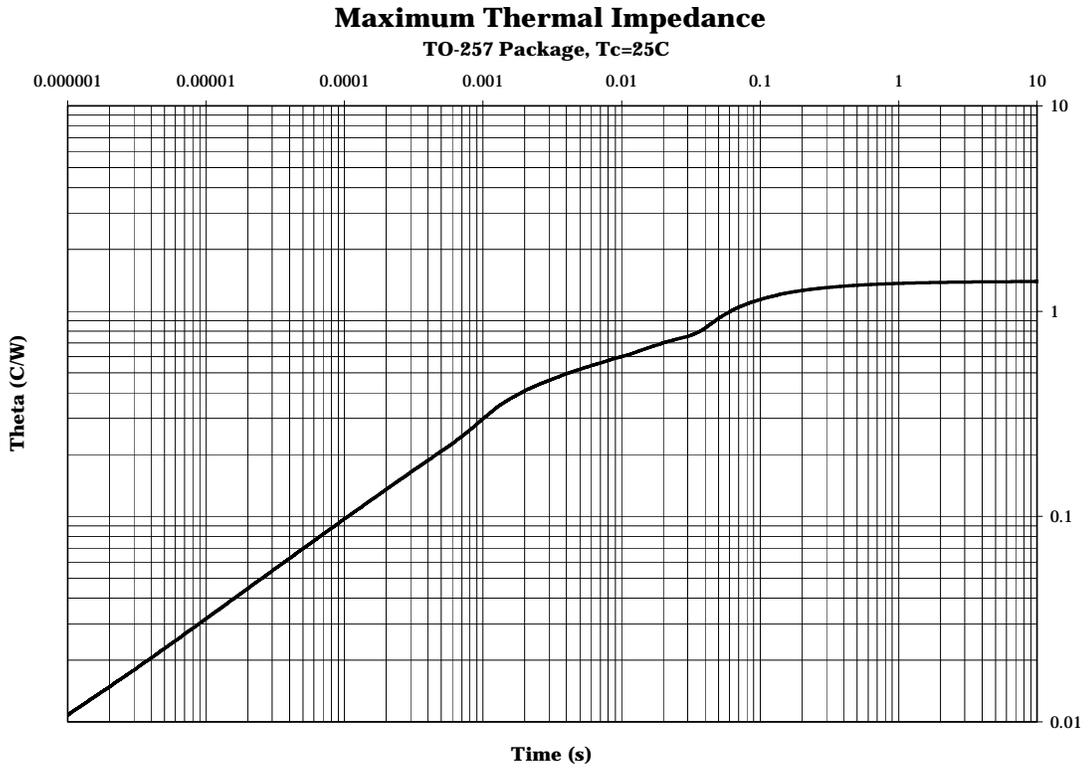
Note: Maximum Finish-Alloy Temperature = +175°C for lead tin solder alloys.

FIGURE 4. Derating for TO-257AA types.



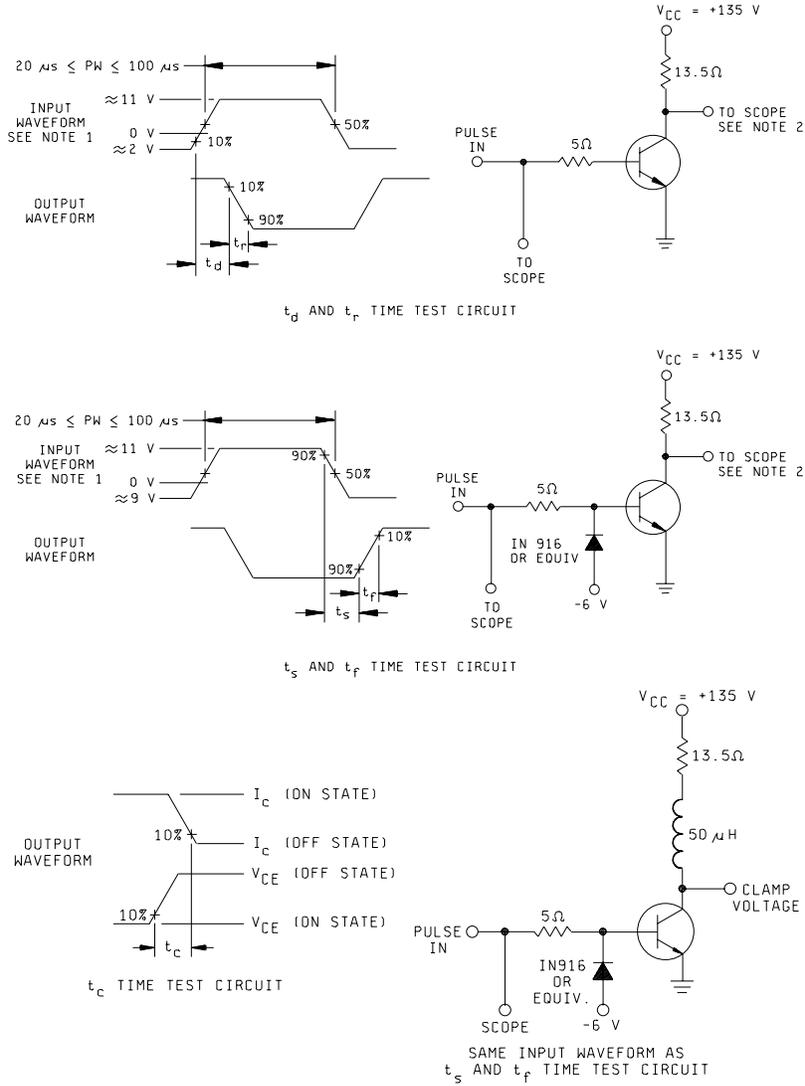
$R_{\theta JC} = 1^{\circ}\text{C/W}$

FIGURE 5. Thermal impedance graph for 2N6674T1 and 2N6675T1 (TO-254).



$$R_{\theta JC} = 1.3^{\circ}\text{C/W}$$

FIGURE 6. Thermal impedance graph for 2N6674T3 and 2N6675T3 (TO-257).



NOTES:

1. The rise time (t_r) of the applied pulse shall be ≤ 20 ns; duty cycle ≤ 2 percent; generator source impedance shall be 500Ω .
2. Output sampling oscilloscope: $Z_{in} \geq 10$ k Ω ; $C_{in} \leq 13$ pF; rise time ≤ 20 ns.

FIGURE 7. Pulse response test circuit.

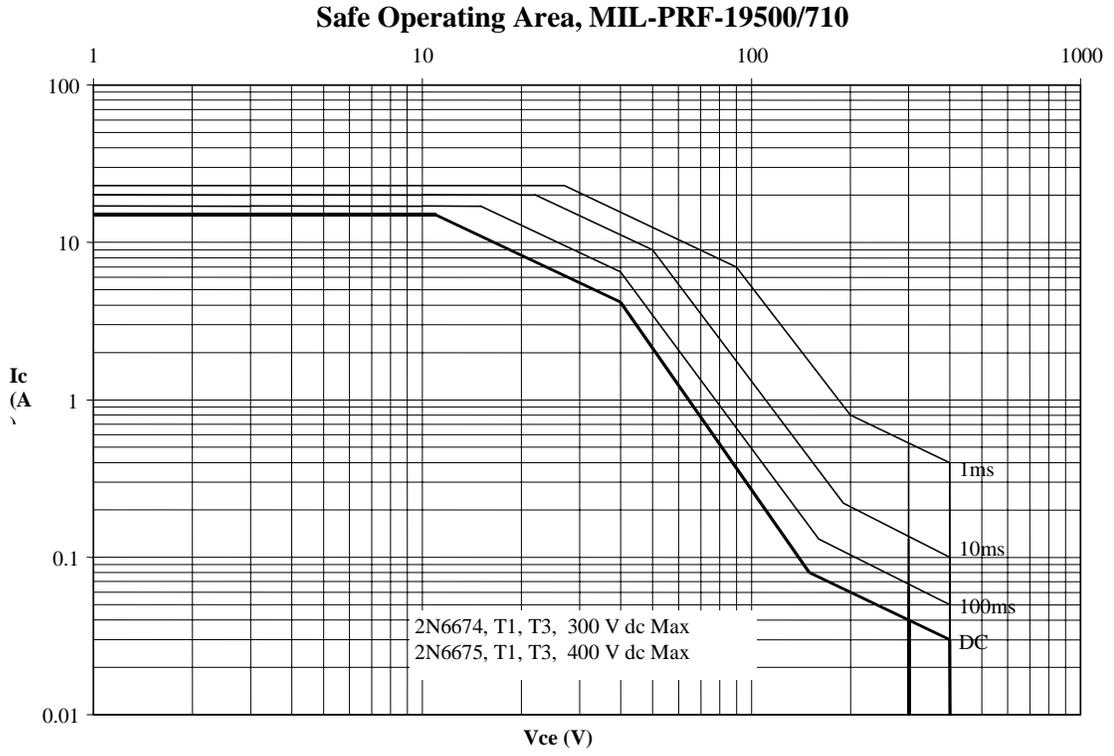


FIGURE 8. Safe operating area curve for all devices at $T_{(case)} = +25^{\circ}C$.

5. PACKAGING

5.1 Packaging. For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When actual packaging of materiel is to be performed by DoD personnel, these personnel need to contact the responsible packaging activity to ascertain requisite packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activity within the Military Department or Defense Agency, or within the Military Department's System Command. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

(This section contains information of a general or explanatory nature that may be helpful, but is not mandatory.)

6.1 Intended use. The notes specified in MIL-PRF-19500 are applicable to this specification.

6.2 Acquisition requirements. Acquisition documents must specify the following:

- a. Title, number, and date of this specification.
- b. Issue of DoDISS to be cited in the solicitation, and if required, the specific issue of individual documents referenced (see 2.2.1).
- c. Packaging requirements (see 5.1).
- d. Lead finish (see 3.4.1).

6.3 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers' List (QML) whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from Defense Supply Center, Columbus, ATTN: DSCC/VQE, P.O. Box 3990, Columbus, OH 43216-5000.

Custodians:
Army - CR
Navy - EC
Air Force - 11
DLA - CC

Preparing activity:
DLA - CC

(Project 5961-2715)

Review activities:
Army - AR, AV, MI
Air Force - 19, 70, 99

STANDARDIZATION DOCUMENT IMPROVEMENT PROPOSAL

INSTRUCTIONS

1. The preparing activity must complete blocks 1, 2, 3, and 8. In block 1, both the document number and revision letter should be given.
2. The submitter of this form must complete blocks 4, 5, 6, and 7.
3. The preparing activity must provide a reply within 30 days from receipt of the form.

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I RECOMMEND A CHANGE:	1. DOCUMENT NUMBER MIL-PRF-19500/710	2. DOCUMENT DATE 7 May 2003
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3. **DOCUMENT TITLE** SEMICONDUCTOR DEVICE, TRANSISTOR, NPN, SILICON, POWER TYPES 2N6674T1, 2N6675T1, 2N6674T3, 2N6675T3 JAN, JANTX, AND JANTXV

4. **NATURE OF CHANGE** (Identify paragraph number and include proposed rewrite, if possible. Attach extra sheets as needed.)

5. **REASON FOR RECOMMENDATION**

6. **SUBMITTER**

a. NAME (Last, First, Middle initial)	b. ORGANIZATION	
c. ADDRESS (Include Zip Code)	d. TELEPHONE (Include Area Code) COMMERCIAL DSN FAX EMAIL	7. DATE SUBMITTED

8. **PREPARING ACTIVITY**

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c. ADDRESS Defense Supply Center Columbus ATTN: DSCC-VAC P.O. Box 3990 Columbus, OH 43216-5000	IF YOU DO NOT RECEIVE A REPLY WITHIN 45 DAYS, CONTACT: Defense Standardization Program Office (DLSC-LM) 8725 John J. Kingman, Suite 2533 Fort Belvoir, VA 22060-6221 Telephone (703) 767-6888 DSN 427-6888